

Eunsung Shin

List of Publications by Year in descending order

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Version: 2024-02-01

15
papers

151
citations

1478505

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1588992

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15
all docs

15
docs citations

15
times ranked

259
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural, electrical, and electromagnetic properties of nanostructured vanadium dioxide thin films. , 2021, , 65-90.		3
2	Experimental Demonstration of Vanadium Dioxide Phase Change Thin Film Based Tunable Spiral Inductors. ECS Journal of Solid State Science and Technology, 2020, 9, 075003.	1.8	2
3	Analysis of Lithium Niobate Memristor Devices for Neuromorphic Programability. , 2019, , .		2
4	Tungsten-doped vanadium dioxide thin film based tunable antenna. Materials Research Bulletin, 2018, 101, 287-290.	5.2	11
5	Filament formation in lithium niobate memristors supports neuromorphic programming capability. Neural Computing and Applications, 2018, 30, 3773-3779.	5.6	15
6	Experimental Study of Memristors for use in Neuromorphic Computing. , 2018, , .		4
7	Tunable Inductors Using Integrated Vanadium Dioxide Phase Change Thin Films. Advances in Condensed Matter Physics, 2018, 2018, 1-7.	1.1	1
8	Experimental study of LiNbO3 memristors for use in neuromorphic computing. Microelectronic Engineering, 2017, 168, 37-40.	2.4	34
9	Tunable inductors using vanadium dioxide as the control material. Microwave and Optical Technology Letters, 2017, 59, 1057-1061.	1.4	12
10	Naturally formed ultrathin V2O5 heteroepitaxial layer on VO2/sapphire(001) film. Applied Surface Science, 2017, 419, 365-372.	6.1	14
11	Methods for high resolution programming in lithium niobate memristors for neuromorphic hardware. , 2017, , .		3
12	Design of tunable shunt and series interdigital capacitors based on vanadium dioxide thin film. , 2017, , .		3
13	Memristor devices for use in neuromorphic systems. , 2016, , .		4
14	Lithium based memristive device. , 2015, , .		9
15	Vanadium Oxide Thin-Film Variable Resistor-Based RF Switches. IEEE Transactions on Electron Devices, 2015, 62, 2959-2965.	3.0	34